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TECHNOLOGY CENTER 2800

PATENT APPLICATION
RESPONSE UNDER 37 CFR §1.116
EXPEDITED PROCEDURE
TECHNOLOGY CENTER ART UNIT 2811

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tomoyoshi KUSHIDA ✓

Group Art Unit: 2811

Application No.: 09/435,766 ✓

Examiner: Steven Ho Yin Loke

Filed: November 8, 1999 ✓

Docket No.: 104361

For: SEMICONDUCTOR DEVICE ✓

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the December 10, 2002 Office Action, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 12, 26 and 30 as follows:

12. (Six Times Amended) A semiconductor device comprising:
- a substrate having a first conductive type;
 - a drift region having the first conductive type and disposed on the substrate;
 - a channel region having a second conductive type different from the first conductive type and provided on the drift region;
 - a gate region provided so as to surround at least the channel region via an insulation film; and

figs. 10A, 10B,
P. 8
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